

Art Unit: 2811

a fourth device region of the first conductivity type provided in said second well, said third and fourth device regions being disposed not to oppose each other face-to-face, with a second section of said well isolation structure disposed between said third and fourth device regions, said fourth device region being provided positioned separately from and adjacent to said second device region;

wherein said second section of said well isolation structure is wider than said first section of said well isolation structure. ~~a first width of said well isolation structure between said first and second device regions is smaller than a second width of said well isolation structure between said third and fourth device regions.~~

Claim 17 (currently amended) The semiconductor device according to claim 16, wherein said first, second, third and fourth device regions have a substantially same configuration shape.

Claim 18 (currently amended) A semiconductor device comprising:

a first well of p type and a second well of n type disposed adjacent to each other; a straight well isolation structure comprising a shallow trench formed on a boundary of said first and second wells; a pair of a first device region of n type and a second device region of p type, said first and second device regions being disposed to oppose each other face-to-face, with a first section of said well isolation structure disposed between said first device region and said second device region;

a third device region of n type and fourth device region of p type, said third and fourth device regions being disposed not to oppose each other face-to-face, with a second section of said well isolation structure disposed between said third device region and said fourth device region;

wherein said first and third device regions are adjacent to each other and separately provided positioned in said first well, and said third second and fourth device regions are adjacent to each other and separately provided positioned in said second well, and a first width said second section of said well isolation structure between said

~~first and second device regions is smaller wider than a said second-first section of said well isolation structure between said third and fourth device regions.~~

Allowable Subject Matter

2. Claims 16-18 are allowed.

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. References A-C are cited as being related to a trench isolation structure.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shouxiang Hu whose telephone number is 571-272-1654. The examiner can normally be reached on Monday through Thursday, 7:30 AM to 6:00 PM.

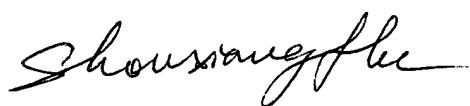
If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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SH

March 17, 2004



SHOUXIANG HU
PRIMARY EXAMINER